IN THE CLAIMS:

1. (Currently Amended) A solid-state imaging element, comprising:

unit pixels, arranged in a matrix form, each of which have a photoelectric conversion transfer element elements, a transfer switch switches for transferring charge charges stored in said photoelectric conversion element transfer elements, a charge store part parts for storing eharges charge transferred by said transfer switch switches, a reset switch switches for resetting said charge store part parts, and an amplifying element elements for outputting signals a signal in accordance with the a potential of said charge in said charge store part parts to vertical signal lines;

a vertical scanning circuit for selecting pixels in units of rows by controlling a reset potential afforded applied to selected ones of said reset switches;

a horizontal scanning circuit for sequentially selecting signals output to said vertical signal lines in units of columns; and

an output circuit for outputting signals selected by said horizontal scanning circuit via horizontal signal lines.

2. (Currently Amended) A solid-state imaging element as claimed in claim 1, wherein said vertical scanning circuit affords applies vertical selection pulses sequentially output during vertical scanning to said reset switches as a reset potential thereof.

- 3. (Original) A solid-state imaging element as claimed in claim 1, wherein said charge store part is floating diffusion.
- 4. (Currently Amended) A solld-state imaging element as claimed in claim 1, wherein said reset switches emprise a are depression type transistors transistors.
- 5. (Original) A solid-state imaging element as claimed in claim 1, wherein said output circuit outputs signals read into said vertical signal lines in voltage mode.
- 6. (Original) A solid-state imaging element as claimed in claim 1, wherein said output circuit outputs signals read into said vertical signal lines in current mode.
- 7. (Currently Amended) A solid-state imaging element as claimed in claim 1, wherein said unit pixels include an overflow path between said photoelectric conversion transfer element and an area to which a pixel source voltage is applied afforded, said overflow path being used to discharge excess charges of said photoelectric conversion transfer element.
- 8. (Currently Amended) A solid-state imaging element as claimed in claim 1, wherein a negative potential is applied to the control electrode of each of said transfer switches.

9. (Previously Canceled)

10. (Previously Canceled)

11. (Previously Canceled)

12. (Currently Amended) A method for driving a solid-state imaging element which includes including unit pixels, arranged in a matrix form, each of which have a photoelectric conversion element transfer elements, a transfer switches switch for transferring charges charge stored in said photoelectric conversion element transfer elements, a charge store parts part for storing charges charge transferred by said transfer switch switches, a reset switch switches for resetting said charge store part parts, and an amplifying element elements for outputting signals a signal in accordance with the a potential of said charge store part parts to vertical signal lines, said method comprising the step of:

selecting pixels in units of rows by controlling a reset potential <u>applied</u> <u>afforded to</u> <u>selected ones of</u> said reset switches.

13. (Original) A method for driving a solid state imaging element as claimed in claim 12, further comprising the step of:

outputting signals read into said vertical signal lines in voltage mode.

14. (Original) A method for driving a solid-state imaging element as claimed in claim 12, further comprising the step of:

outputting signals read into said vertical signal lines in current mode.

Blot

15. (Currently Amended) A camera system using a solid-state imaging element as an imaging device, said solid-state imaging element, comprising:

unit pixels, arranged in a matrix form, each of which have a photoelectric conversion element transfer elements, a transfer switch switches for transferring charges charge stored in said photoelectric conversion element transfer elements, a charge store part parts for storing charges charge transferred by said transfer switch switches, a reset switch switches for resetting said charge store part parts, and an amplifying element elements for outputting signals a signal in accordance with the a potential of said charge store part parts to vertical signal lines;

a vertical scanning circuit for selecting pixels in units of rows by controlling a reset potential afforded applied to selected reset switches said reset switch;

a horizontal scanning circuit for sequentially selecting signals output to said vertical signal lines in units of columns; and

an output circuit for outputting signals selected by said horizontal scanning circuit via horizontal signal lines.

Please add the following new claims:

16. (Newly Added) The solid-state imaging element of claim 1, wherein a falling edge of the reset pulse triggers reading of a reference level.

- 17. (Newly Added) The solid-state imaging element of claim 1, wherein a changing state of the reset pulse and a selection pulse initiates a pixel reading operation.
- 18. (Newly Added) The method of driving a solid-state imaging element of claim

 12, further comprising triggering reading of a reference level with a falling edge of the reset pulse.
- 19. (Newly Added) The method of driving a solid-state imaging element of claim

 12, wherein a changing state of the reset pulse and a selection pulse initiates a pixel reading operation.
- 20. (Newly Added) The camera system of claim 15, wherein a falling edge of the reset pulse triggers reading of a reference level.
- 21. (Newly Added) The camera system of claim 15, wherein a changing state of the reset pulse and a selection pulse initiates a pixel reading operation.